

Abstract of the Disclosure

A method for fabricating a semiconductor device includes the steps of: (a) forming a plurality of conductive patterns on a substrate in a cell region and a peripheral circuit region; (b) forming an insulation layer on an entire surface of the resulting structure from the step (a); (c) forming a plurality of plugs in the cell region and simultaneously forming a dummy pattern in a region between the cell region and the peripheral circuit region, each plug and the dummy pattern being contacted to the substrate allocated between the conductive patterns by passing through the insulation layer; (d) forming a photoresist pattern masking the resulting structure in the cell region; and (e) removing the insulation layer in the peripheral circuit region by performing a wet etching process with use of the photoresist pattern as an etch mask to thereby expose a surface of the substrate in the peripheral circuit region.